

O P P 2 Q R S T U V W X

silicon PNP transistor in a SOT-363 Plastic Package.

$\beta_{FE} Z [\quad V_{CE(sat)} X C D \setminus] X$

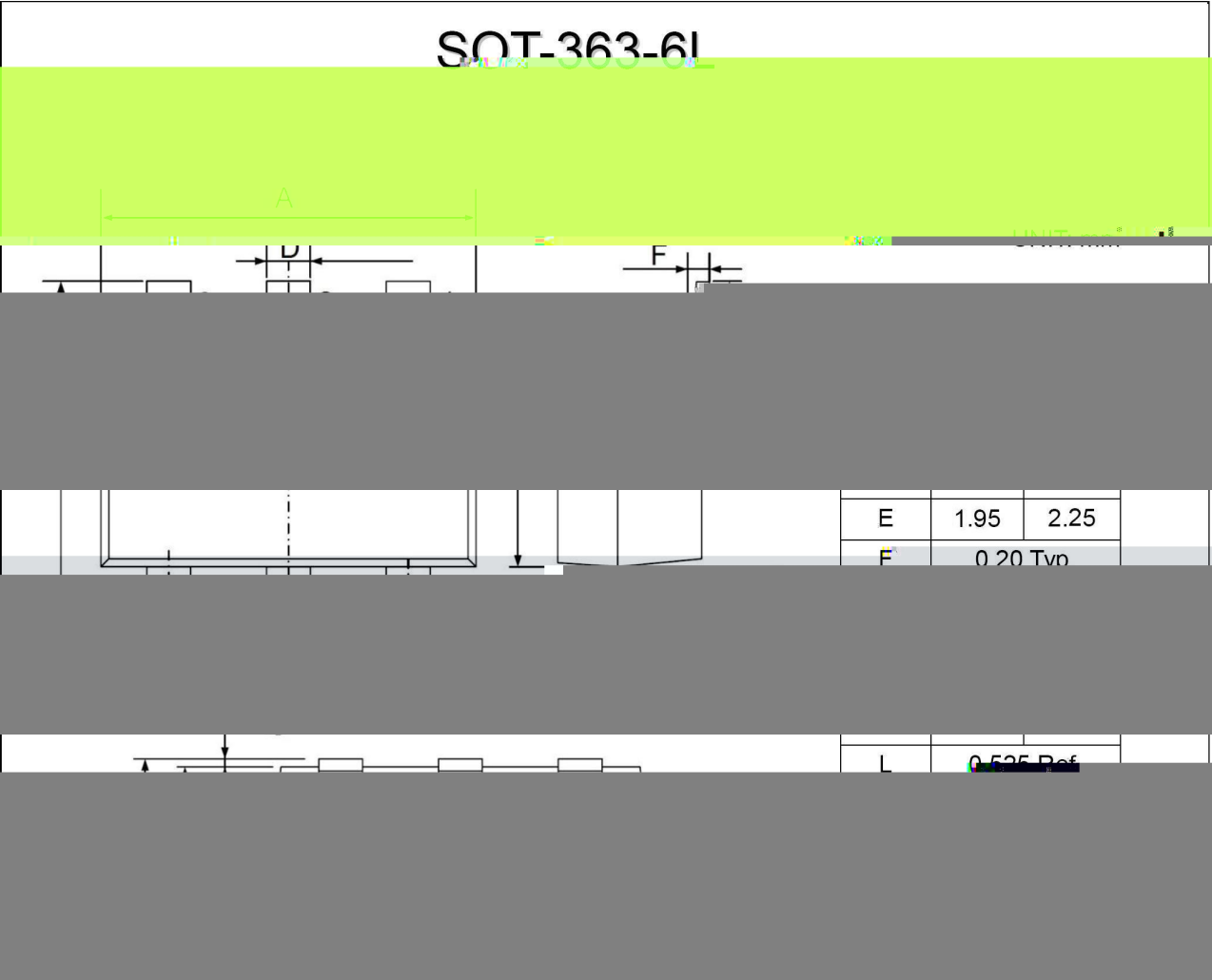
High DC Current Gain, Low Collector to Emitter Saturation Voltage. HF Product.

$\wedge _ \backslash a b c) d e X$

General purpose amplifier and switching.

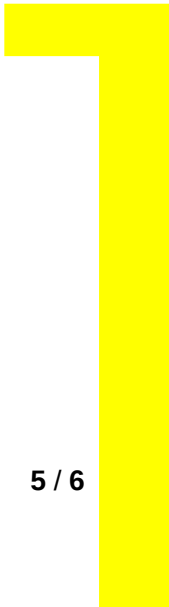
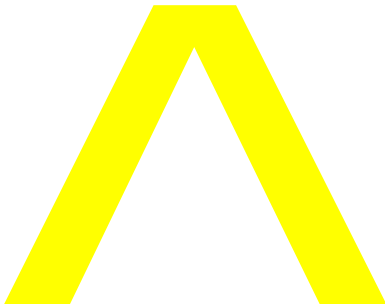
g h Parameter	i j Symbol	h k Rating	l m Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-200	mA

/ Package Dimensions



/ Marking Instructions

v w f
● f x y 1 z {
A2 f x u j | '
***: x } \ ~ j | ' Z } \ ~ j i ¢



() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|---------|-----------|---|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5℃	Time:10±1 sec
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/ Packaging SPEC.

/ REEL

 Package Type
 封装形式

Units 包装数量

DimensCeC

O